3DD253(254),3DD255(256),3DD257(258)

NPN Silicon Low Frequency High Power Transistor

Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications				
			3DD253		3DD255		3DD257
			A	B	C	D	E
Collector-Emitter Voltage	V_{CEO}	V	300	400	500	600	700
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	300	400	500	600	700
			3DD253: I_C=1mA		3DD255: I_C=1mA		3DD257: I_C=3mA
Emitter-Base Voltage	V_{EBO}	V	5		5		5
Max. Collector Current	I_{CM}	A	1		1.5		2
Max. Collector Dissipation	P_{CM}	W	10 (T_C≤75°C)		20 (T_C≤75°C)		30 (T_C≤75°C)
Junction Temperature	T_{jm}	°C	175				
Storage Temperature	T_{stg}	°C	-55~+175				
Collector-Emitter Leakage Current	I_{CEO}	mA	0.5 (V_{CE}=100V)				
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.2 (I_C=0.5A,I_B=0.1A)		1.2 (I_C=0.75A,I_B=0.15A)		1.2 (I_C=1.0A,I_B=0.2A)
DC Current Gain	h_{FE}		Max.:180,Min.:7 (V_{CE}=10V,I_C=0.5A)		Max.:180, Min.:7 (V_{CE}=10V,I_C=0.75A)		Max.:180, Min.:7 (V_{CE}=10V,I_C=1.0A)
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥5 (I_E=0.5mA)				

h_{FE} Colored:

Color	Brown	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	7~15	15~25	25~40	40~55	55~80	80~120	120~180

Outline and Dimensions:

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